

Schottky barrier diode

RB521S-30

●Applications

Low current rectification

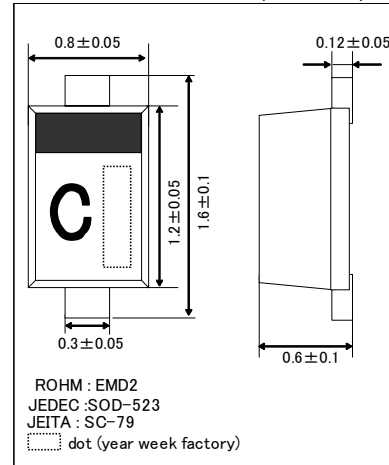
●Features

- 1) Ultra Small mold type. (EMD2)
- 2) Low V_F
- 3) High reliability.

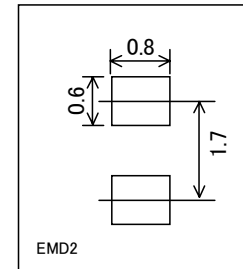
●Construction

Silicon epitaxial planar

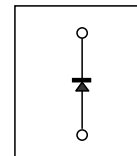
● External dimensions (Unit : mm)



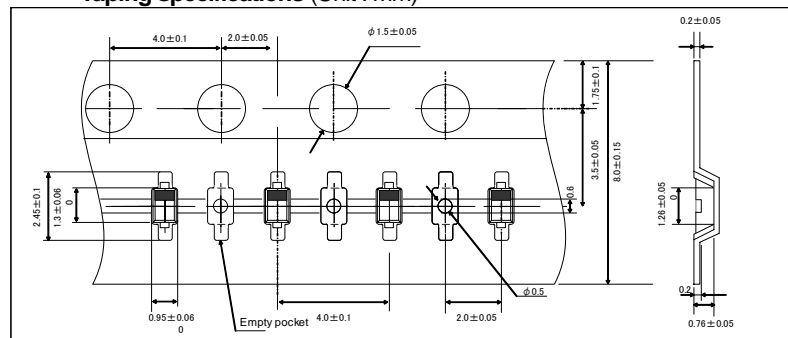
● Land size figure (Unit : mm)



●Structure



● Taping specifications (Unit : mm)

●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

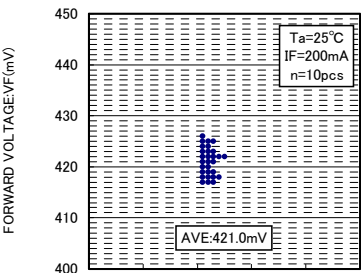
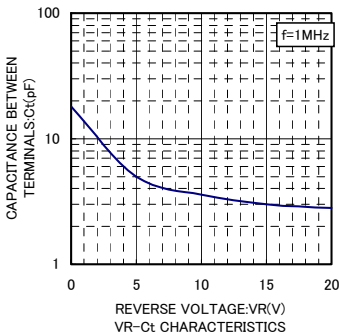
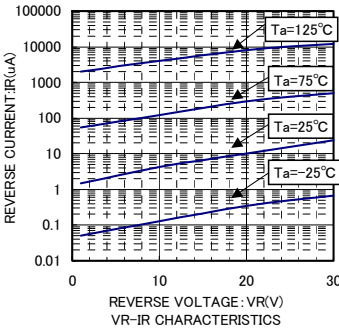
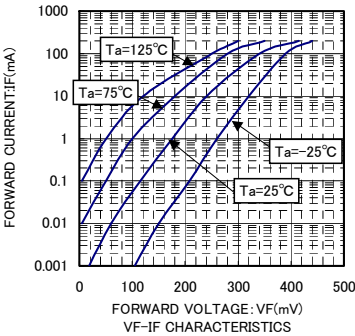
Parameter	Symbol	Limits	Unit
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_o	200	mA
Forward current surge peak (60Hz · 1cyc)	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +125	$^\circ\text{C}$

●Electrical characteristics ($T_a=25^\circ\text{C}$)

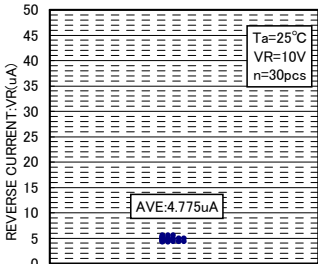
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.50	V	$I_F=200\text{mA}$
Reverse current	I_R	-	-	30	μA	$V_R=10\text{V}$

Diodes

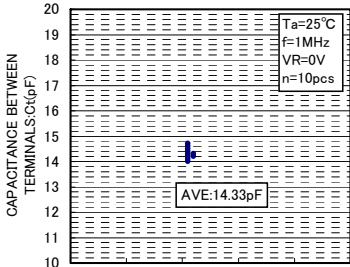
●Electrical characteristic curves (Ta=25°C)



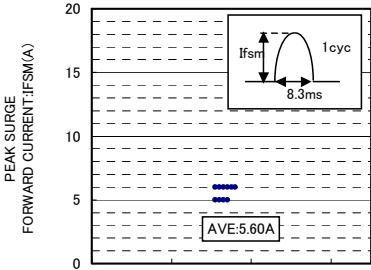
VF DISPERSION MAP



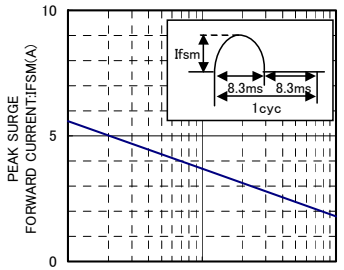
IR DISPERSION MAP



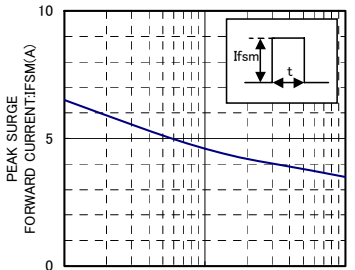
Ct DISPERSION MAP



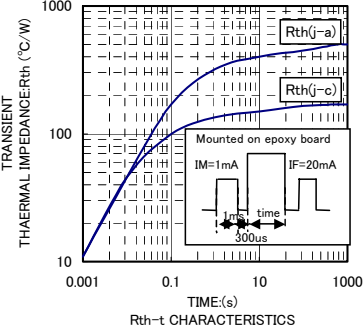
IFSM DISPERSION MAP



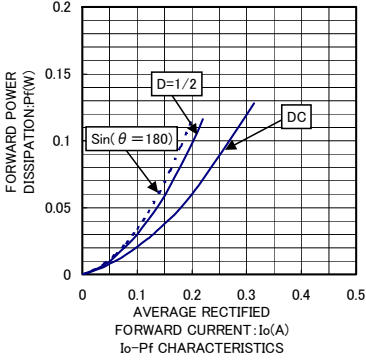
NUMBER OF CYCLES
IFSM-CYCLE CHARACTERISTICS



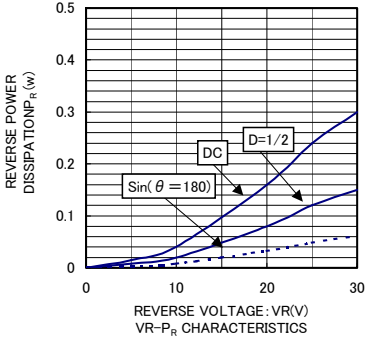
TIME:t(ms)
IFSM-t CHARACTERISTICS



Rth-t CHARACTERISTICS

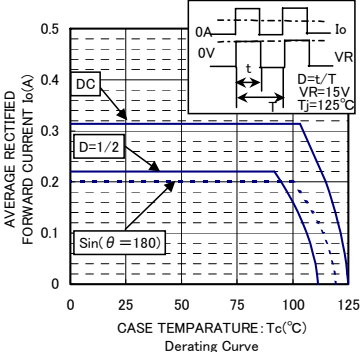
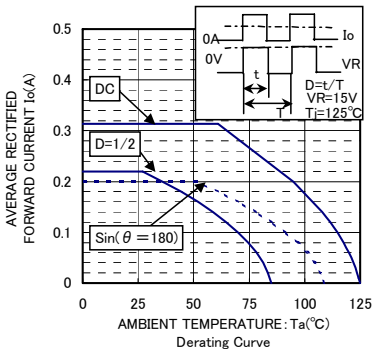


AVERAGE RECTIFIED
FORWARD CURRENT: Io(A)
Io-Pf CHARACTERISTICS



REVERSE VOLTAGE: VR(V)
VR-Pr CHARACTERISTICS

Diodes



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